

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	2	(variable adj resistor) same diode same memory and cell and column adj address	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/22 07:04
S1	1327	variable adj resistor and bipolar adj transistor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/07 18:08
S2	4	variable adj resistor and bipolar adj transistor and perovskite	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/21 17:43
S3	4	(variable adj resistor or (varistor)) and bipolar adj transistor and perovskite	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/21 17:43
S4	38	(variable adj resistor or (varistor)) and transistor and perovskite	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/07 18:23
S5	12	(variable adj resistor or (varistor)) and transistor and perovskite and matrix	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/21 17:43
S6	10	(variable adj resistor or (varistor)) and transistor and perovskite and matrix and bit	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/07 18:23
S7	6	(variable adj resistor or (varistor)) and transistor and perovskite and matrix and bit and drain	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/21 17:43
S8	5	(variable adj resistor or (varistor)) and transistor and perovskite and matrix and bit and row	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/07 18:24

S9	5	(variable adj resistor or (varistor)) and transistor and perovskite and matrix and bit and column	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/07 19:09
S11	421	(257/537).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/21 17:41
S12	843	(257/379).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/07 19:13
S13	1095	(257/390).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/07 19:14
S14	1206	(257/288).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/07 19:15
S15	399	(257/528).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/07 19:15
S16	11	(variable adj resistor or (varistor)) and \$3fet and perovskite	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/07 19:17
S17	0	varistor same bipolar adj transistor and memory	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/09 22:57
S18	9	varistor same bipolar adj transistor and memory	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/09 23:01
S19	47	(variable adj resistor) same bipolar adj transistor and memory	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/09 23:11

S20	302	(variable adj resistor) same diode and memory and cell	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/09 23:11
S21	4	(variable adj resistor) same diode and memory and cell and perovskite	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/21 17:41
S22	65	(variable adj resistor) same diode same memory and cell	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/21 17:42
S23	37	(variable adj resistor) with diode same memory and cell	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/10 00:28
S24	0	bipolar and matrix and varistor and perovskite	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/10 00:29
S25	2	bipolar and varistor and perovskite	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/21 17:42
S26	1448	(257/295).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/10 00:49
S27	236	(365/148).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/21 17:37
S28	1709	(365/145).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/21 17:37
S29	1173	(365/158).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/21 17:37

S30	1294	(257/536).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/21 17:41
S31	435	(257/537).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/21 17:41
S32	435	(257/537).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/21 17:41
S33	7	(variable adj resistor) same diode and memory and cell and perovskite	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/21 17:42
S34	75	(variable adj resistor) same diode same memory and cell	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/22 07:04
S35	2	bipolar and varistor and perovskite	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/21 17:42
S36	9	(variable adj resistor or (varistor)) and transistor and perovskite and matrix and bit and drain	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/21 17:43
S37	4	variable adj resistor and bipolar adj transistor and perovskite	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/21 17:43
S38	17	(variable adj resistor or (varistor)) and transistor and perovskite and matrix	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/21 17:44
S39	4	(variable adj resistor or (varistor)) and bipolar adj transistor and perovskite	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/21 17:43